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(54) Adduct of a dialkylgalliumazide with hydrazine for MOCVD of GaN

Hydrazinaddukt von Dialkylgalliumazid als molekulare Vorstufe für Gasphasenabscheidung von GaN

Composé d'addition constitué de dialkylgallium azide et d'hydrazine pour dépôt de GaN sous forme de films par dépôt chimique en phase vapeur

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Description**Field of the Invention**

5 [0001] The present invention relates to a novel, volatile organogallium compound; a process of the preparation thereof; and a metal organic chemical vapor deposition (MOCVD) process for forming a gallium nitride film on a substrate using said compound.

Background of the Invention

10 [0002] GaN films are used in blue electroluminescent diodes and in generating blue laser. There have been reported studies to prepare such films by metal organic chemical vapor deposition (MOCVD) using such organogallium compounds as triethylgallium • amine adduct, bis(dialkyl-μ -amido-gallium), bis[dimethyl(1,1-dimethylhydrazido)gallium] and the like (see J. E. Andrews and M. A. Littlejohn, *J. Electrochem. Soc.*, 122, 1273 (1975); United States Patent 4,975,299 and European Patent Application 0 295 467 A2; and V. Lakhota, D. A. Neumayer, A. H. Cowley, R. A. Jones and J. G. Ekerdt, *Chem. Mater.*, 7, 546 (1995)).

[0003] However, as these GaN precursors exist in the form of dimers or trimers, which are often solids at room temperature, they are difficult to handle in MOCVD due mainly to their low vapor pressures. Further, these conventional precursors are known to give GaN films which have lattice nitrogen defects.

20 [0004] The present inventors have endeavored to develop a novel compound which can be employed in an improved MOCVD process for preparing a GaN film of improved quality, and have discovered that an azidodialkylgallium hydrazine adduct has high volatility and can be effectively used in MOCVD to form a GaN film having no significant amount of nitrogen defects.

Summary of the Invention

[0005] Accordingly, it is an object of the present invention to provide a novel organogallium compound which has high volatility and can be advantageously used in forming a GaN film of improved quality.

[0006] It is another object of the present invention to provide a process for preparing said compound.

30 [0007] It is a further object of the present invention to provide a process for depositing a GaN film on a substrate using said compound.

[0008] In accordance with one aspect of the present invention, there is provided an organogallium compound of formula(I):



wherein, R¹ and R² are each independently C₁₋₅ alkyl; and R³ and R⁴ are each independently hydrogen or C₁₋₅ alkyl.

40 [0009] In accordance with another aspect of the present invention, there is provided a process for preparing a compound of formula(I) comprising the steps of: (a) reacting a compound of formula(II) with a compound of formula(III) to give a compound of formula(IV), and (b) reacting the compound of formula(IV) with sodium azide:



wherein, X is halogen; R³ and R⁴ are the same as defined in formula(I) above; and R is C₁₋₅ alkyl.

55 [0010] In accordance with further another aspect of the present invention, there is provided a process for depositing a GaN film on a substrate which comprises bringing the vapor of the compound of formula(I) into contact with a substrate heated to a temperature ranging from 400 to 800°C.

Preferred embodiments of the present invention are defined in the dependent claims.

Brief Description of the Drawings

[0011] The above and other objects and features of the present invention will become apparent from the following description of the invention taken in conjunction with the following accompanying drawings, which respectively show:

FIGs. 1 and 2 : X-ray photoelectron and X-ray diffraction spectra of the GaN film obtained in Example 9, respectively;

FIG. 3 : X-ray diffraction spectrum of the GaN film obtained in Example 10;

FIG. 4 : X-ray diffraction spectrum of the GaN film obtained in Example 11;

FIGs. 5 and 6 : X-ray photoelectron and X-ray diffraction spectra of the GaN film obtained in Example 12, respectively;

FIG. 7 : X-ray diffraction spectrum of the GaN film obtained in Example 13; and

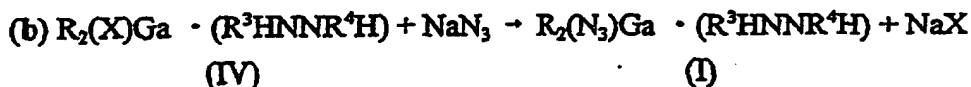
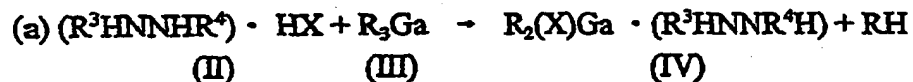
FIG. 8 : X-ray diffraction spectrum of the GaN film obtained in Example 14.

Detailed Description of the Invention

[0012] The novel compound of formula(I) of the present invention is an azidodialkylgallium complexed with a hydrazine derivative, wherein the nitrogen atom of the azido group bonded to gallium is retained in the formation of a GaN film in MOCVD, while the other nitrogen atoms of the azido group are eliminated as N₂. The hydrazine ligand acts to prevent the compound of formula(I) from forming an oligomeric form.

[0013] Among the inventive organogallium compounds, azidodimethylgallium • methylhydrazine and azidodiethylgallium • methylhydrazine are preferred since they are liquids at room temperature.

[0014] In accordance with the present invention, the compound of formula(I) may be prepared by (a) reacting a compound of formula(II) with a compound of formula(III) to give a compound of formula(IV), and (b) reacting the compound of formula(IV) with sodium azide, as follows:



wherein, X, R³, R⁴ and R have the same meanings as defined above, and X is preferably chlorine, bromine or iodine.

[0015] In step (a), the compound of formula(II) is reacted with the compound of formula(III) in a stoichiometric ratio at a temperature ranging from -70 to 10°C to obtain the compound of formula(IV). Further, in step (b), the compound of formula(IV) obtained in step (a) is reacted with sodium azide in a stoichiometric ratio at a temperature ranging from 70 to 100°C to prepare the inventive organogallium compound of formula(I).

[0016] The reaction steps (a) and (b) may be respectively conducted in an organic solvent such as tetrahydrofuran, acetonitrile, diethylether, toluene and a mixture thereof, under an inert gas atmosphere.

[0017] The compound of formula(I) can be vaporized at a temperature ranging from 40 to 100°C under a pressure ranging from 1.3·10⁻⁴ to 1.3 Pa (10⁻⁶ to 10⁻² Torr).

[0018] In accordance with the present invention, a GaN film may be deposited on a substrate by bringing the vapor of the compound of formula(I) into contact with the surface of a substrate heated to a temperature ranging from 400 to 800°C.

[0019] The substrate which may be used in practicing the present invention is any inorganic solid that is stable at or above the film deposition temperature and examples thereof include glass, quartz, silicon, gallium arsenide, sapphire, alkali metal niobate and alkaline earth metal titanate, among which a single crystal of silicon is preferred when the coated substrate is intended for use in electronic applications.

[0020] The following Examples are given for the purpose of illustration.

Synthesis of Chlorodialkylgallium · Hydrazine Derivatives (Compound(IV))Preparation 1: Chlorodimethylgallium · hydrazine

[0021] 1.0 g of hydrazine hydrochloride was suspended in tetrahydrofuran and 1.7 g of trimethylgallium was added thereto at 0°C over a period of 15 minutes with stirring. The mixture was stirred at room temperature for 5 hours, and then, the solvent was removed under a reduced pressure. 2.1 g of the title compound was obtained in the form of a white solid having a melting point of 66°C.

[0022] The title compound thus obtained was subjected to ¹H-NMR(acetonitrile-*d*₃, ppm): -0.30(s, 6H, Ga-CH₃) and 4.21(br, 4H, N-H).

Preparation 2 : Chlorodimethylgallium · methylhydrazine

[0023] The procedure of Preparation 1 was repeated using 1.0 g of methylhydrazine hydrochloride and 1.4 g of trimethylgallium to obtain 1.8 g of the title compound in the form of a colorless liquid.

[0024] The title compound thus obtained was subjected to ¹H-NMR(acetonitrile-*d*₃, ppm): -0.30(s, 6H, Ga-CH₃), 2.55(s, 3H, NCH₃) and 4.27(br, 3H, N-H).

Preparation 3 : Chlorodimethylgallium · t-butylhydrazine

[0025] The procedure of Preparation 1 was repeated using 2.0 g of t-butylhydrazine hydrochloride and 1.8 g of trimethylgallium to obtain 2.7 g of the title compound in the form of a white solid having a melting point of 94°C.

[0026] The title compound thus obtained was subjected to ¹H-NMR(acetonitrile-*d*₃, ppm): -0.28(s, 6H, Ga-CH₃), 1.09(s, 9H, NC(CH₃)₃) and 4.30(br, 3H, N-H).

Preparation 4: Chlorodiethylgallium · hydrazine

[0027] The procedure of Preparation 1 was repeated using 2.3 g of triethylgallium to obtain 2.5 g of the title compound in the form of a white solid having a melting point of 50°C.

[0028] The title compound thus obtained was subjected to ¹H-NMR(acetonitrile-*d*₃, ppm): 0.38(quartet, 4H, Ga-CH₂CH₃), 1.06(t, 6H, Ga-CH₂CH₃) and 4.17(br, 4H, N-H).

Preparation 5 : Chlorodiethylgallium · methylhydrazine

[0029] The procedure of Preparation 1 was repeated using 1.0 g of methylhydrazine hydrochloride and 1.9 g of triethylgallium to obtain 2.2 g of the title compound in the form of a colorless liquid.

[0030] The title compound thus obtained was subjected to ¹H-NMR(acetonitrile-*d*₃, ppm): 0.38(quartet, 4H, Ga-CH₂CH₃), 1.06(t, 6H, Ga-CH₂CH₃), 2.55(s, 3H, N-CH₃) and 4.21(br, 3H, N-H).

Preparation 6 : Chlorodiethylgallium · t-butylhydrazine

[0031] The procedure of Preparation 1 was repeated using 2.0 g of t-butylhydrazine hydrochloride and 2.5 g of triethylgallium to obtain 3.3 g of the title compound in the form of a white solid having a melting point of 90°C.

[0032] The title compound thus obtained was subjected to ¹H-NMR(acetonitrile-*d*₃, ppm): 0.41(quartet, 4H, Ga-CH₂CH₃), 1.07(t, 6H, Ga-CH₂CH₃), 1.08(s, 9H, N-C(CH₃)₃) and 4.25(br, 3H, N-H).

Synthesis of Azidodialkylgallium · Hydrazine Derivatives (Compound(I))Example 1: Azidodimethylgallium · hydrazine

[0033] 1.0 g of sodium azide was suspended in 10 mL of tetrahydrofuran and added thereto at room temperature with stirring was 10 mL of a tetrahydrofuran solution containing 1.0 g of chlorodimethylgallium hydrazine obtained in Preparation 1. The mixture was refluxed for 12 hours and filtered using a glass filter. The resulting filtrate was distilled under a vacuum to remove the solvent and 0.8 g of the title compound was obtained in the form of a white solid having a melting point of 70°C.

[0034] The title compound thus obtained was subjected to ¹H-NMR and FT-IR. ¹H-NMR(acetonitrile-*d*₃, ppm) showed -0.40(s, 6H, Ga-CH₃) and 4.16(br, 4H, N-H), and FT-IR(ν (cm⁻¹), KBr pellet), 2076.

Example 2 : Azidodimethylgallium · methylhydrazine

[0035] The procedure of Example 1 was repeated using chlorodimethylgallium · methylhydrazine obtained in Preparation 2 to obtain 0.8 g of the title compound in the form of a colorless liquid.

[0036] The title compound thus obtained was subjected to $^1\text{H-NMR}$ and FT-IR. $^1\text{H-NMR}$ (acetonitrile- d_3 , ppm) showed -0.39(s, 6H, Ga- CH_3), 2.54(s, 3H, N- CH_3) and 4.34(br, 4H, N-H), and FT-IR(ν (cm^{-1}), KBr pellet), 2080.

Example 3 : Azidodimethylgallium · t-butylhydrazine

[0037] The procedure of Example 1 was repeated using chlorodimethylgallium · t-butylhydrazine obtained in Preparation 3 to obtain 0.8 g of the title compound in the form of a white solid having a melting point of 95 °C.

[0038] The title compound thus obtained was subjected to $^1\text{H-NMR}$ and FT-IR. $^1\text{H-NMR}$ (acetonitrile- d_3 , ppm) showed -0.32(s, 6H, Ga- CH_3), 1.09(s, 9H, N- $\text{C}(\text{CH}_3)_3$) and 4.32(br, 3H, N-H), and FT-IR(ν (cm^{-1}), KBr pellet), 2084.

Example 4 : Azidodiethylgallium · hydrazine

[0039] The procedure of Example 1 was repeated using chlorodiethylgallium · hydrazine obtained in Preparation 4 to obtain 0.9 g of the title compound in the form of a white solid having a melting point of 97°C.

[0040] The title compound thus obtained was subjected to $^1\text{H-NMR}$ and FT-IR. $^1\text{H-NMR}$ (acetonitrile- d_3 , ppm) showed 0.31(quartet, 4H, Ga- CH_2CH_3), 1.06(t, 6H, Ga- CH_2CH_3) and 4.00(br, 4H, N-H), and FT-IR(ν (cm^{-1}), KBr pellet), 2094.

Example 5 : Azidodiethylgallium · methylhydrazine

[0041] The procedure of Example 1 was repeated using chlorodiethylgallium · methylhydrazine obtained in Preparation 5 to obtain 0.8 g of the title compound in the form of a colorless liquid.

[0042] The title compound thus obtained was subjected to $^1\text{H-NMR}$ and FT-IR. $^1\text{H-NMR}$ (acetonitrile- d_3 , ppm) showed 0.38(quartet, 4H, Ga- CH_2CH_3), 1.08(t, 6H, Ga- CH_2CH_3), 2.55(s, 3H, N- CH_3) and 4.32(br, 3H, N-H), and FT-IR(ν (cm^{-1}), KBr pellet), 2085.

Example 6 : Azidodiethylgallium · t-butylhydrazine

[0043] The procedure of Example 1 was repeated using chlorodiethylgallium · t-butylhydrazine obtained in Preparation 6 to obtain 0.8 g of the title compound in the form of a white solid having a melting point of 46°C.

[0044] The title compound thus obtained was subjected to $^1\text{H-NMR}$ and FT-IR. $^1\text{H-NMR}$ (acetonitrile- d_3 , ppm) showed 0.38(quartet, 4H, Ga- CH_2CH_3), 1.08(t, 6H, Ga- CH_2CH_3), 1.08(s, 9H, N- $\text{C}(\text{CH}_3)_3$) and 4.16(br, 3H, N-H), and FT-IR(ν (cm^{-1}), KBr pellet), 2079.

Deposition of GaN FilmExample 7

[0045] A Si(111) substrate was heated to 600°C under an initial pressure of $1.3 \cdot 10^{-4}$ Pa (1.0×10^{-6} Torr). 0.5 g of azidodimethylgallium · hydrazine prepared in Example 1 was vaporized at 80°C and the vapor was conveyed to the surface of the substrate at a total pressure of $2 \cdot 10^{-2}$ Pa (1.5×10^{-4} Torr) for 5 hours to deposit a film thereon.

[0046] The elemental composition of the deposited film surface determined by X-ray photoelectron spectroscopy corresponded to a Ga:N atomic ratio of 1:0.74. Further, an X-ray diffraction analysis showed that the deposited film was crystalline GaN.

Example 8

[0047] A Si(111) substrate was heated to 600°C under an initial pressure of $8.0 \cdot 10^{-5}$ Pa (6.0×10^{-7} Torr). 0.5 g of azidodimethylgallium · methylhydrazine prepared in Example 2 was vaporized at 80°C and the vapor was conveyed to the surface of the substrate at a total pressure of $6.7 \cdot 10^{-3}$ Pa (5.0×10^{-5} Torr) for 5 hours to deposit a film thereon.

[0048] The elemental composition of the deposited film surface determined by X-ray photoelectron spectroscopy corresponded to a Ga:N atomic ratio of 1:0.7. Further, an X-ray diffraction analysis showed that the deposited film was crystalline GaN.

Example 9

[0049] A Si(100) substrate was heated to 600°C under an initial pressure of $36 \cdot 10^{-6}$ Pa (6.0×10^{-6} Torr). 0.5 g of azidodimethylgallium · t-butylhydrazine prepared in Example 3 was vaporized at 75°C and the vapor was conveyed to the surface of the substrate at a total pressure of $1.3 \cdot 10^{-3}$ Pa (1.0×10^{-4} Torr) for 5 hours to deposit a film thereon.

[0050] The elemental composition of the deposited film surface determined by X-ray photoelectron spectroscopy corresponded to a Ga:N atomic ratio of 1:0.71. Further, an X-ray diffraction analysis showed that the deposited film was crystalline GaN film preferentially oriented to the (002) direction. The X-ray photoelectron and X-ray diffraction spectra of the GaN film obtained in Example 9 are shown in FIGs. 1 and 2, respectively.

Example 10

[0051] A Si(111) substrate was heated to 550°C under an initial pressure of 1.3 Pa (1.0×10^{-2} Torr), 0.5 g of azidodiethylgallium · hydrazine prepared in Example 4 was vaporized at 80°C and the vapor was conveyed to the surface of the substrate at a total pressure of 2 Pa (1.5×10^{-2} Torr) for 9.5 hours to deposit a film thereon.

[0052] The elemental composition of the deposited film surface determined by X-ray photoelectron spectroscopy corresponded to a Ga:N atomic ratio of 1:0.84. Further, an X-ray diffraction analysis showed that the deposited film was crystalline GaN preferentially oriented to the (110) direction. The X-ray diffraction spectrum of the GaN film obtained in Example 10 is shown in FIG. 3.

Example 11

[0053] A Si(100) substrate was heated to 500°C under an initial pressure of $2.7 \cdot 10^{-4}$ Pa (2.0×10^{-6} Torr). 0.5 g of azidodiethylgallium · methylhydrazine prepared in Example 5 was vaporized at 75°C and the vapor was conveyed to the surface of the substrate at a total pressure of 53.3 Pa (4.0×10^{-1} Torr) for 3 hours to deposit a film thereon.

[0054] The elemental composition of the deposited film surface determined by X-ray photoelectron spectroscopy corresponded to a Ga:N atomic ratio of 1:0.76. Further, an X-ray diffraction analysis showed that the deposited film was crystalline GaN preferentially oriented to the (002) direction. The X-ray diffraction spectrum of the GaN film obtained in Example 11 is shown in FIG. 4.

Example 12

[0055] A Si(111) substrate was heated to 600°C under an initial pressure of $2.7 \cdot 10^{-5}$ Pa (2.0×10^{-7} Torr), 0.5 g of azidodiethylgallium · methylhydrazine prepared in Example 5 was vaporized at 75°C and the vapor was conveyed to the surface of the substrate at a total pressure of $5.3 \cdot 10^{-2}$ Pa (4.0×10^{-4} Torr) for 3 hours to deposit a film thereon.

[0056] The elemental composition of the deposited film surface determined by X-ray photoelectron spectroscopy corresponded to a Ga:N atomic ratio of 1:0.77. Further, an X-ray diffraction analysis showed that the deposited film was crystalline GaN preferentially oriented to the (002) direction. The X-ray photoelectron and X-ray diffraction spectra of the GaN film obtained in Example 12 are shown in FIGs. 5 and 6, respectively.

Example 13

[0057] A Si(100) substrate was heated to 500°C under an initial pressure of $2.7 \cdot 10^{-5}$ Pa (2.0×10^{-7} Torr). 0.5 g of azidodiethylgallium · t-butylhydrazine prepared in Example 6 was vaporized at 75°C and the vapor was conveyed to the surface of the substrate at a total pressure of $5.3 \cdot 10^{-2}$ Pa (4.0×10^{-4} Torr) for 3 hours to deposit a film thereon.

[0058] The elemental composition of the deposited film surface determined by X-ray photoelectron spectroscopy corresponded to a Ga:N atomic ratio of 1:0.6. Further, an X-ray diffraction analysis showed that the deposited film was crystalline GaN. The X-ray diffraction spectrum of the GaN film obtained in Example 13 is shown in FIG. 7.

Example 14

[0059] A Si(111) substrate was heated to 500°C under an initial pressure of 1.3 Pa (1.0×10^{-2} Torr). 0.5 g of azidodiethylgallium · t-butylhydrazine prepared in Example 6 was vaporized at 75°C and the vapor was conveyed to the surface of the substrate at a total pressure of 2 Pa (1.5×10^{-2} Torr) for 3 hours to deposit a film thereon.

[0060] The elemental composition of the deposited film surface determined by X-ray photoelectron spectroscopy corresponded to a Ga:N atomic ratio of 1:0.85. Further, an X-ray diffraction analysis showed that the deposited film was crystalline GaN. The X-ray diffraction spectrum of the GaN film obtained in Example 14 is shown in FIG. 8.

[0061] As shown above, the organogallium compound of the present invention can be vaporized at a low temperature,

and therefore, it may be effectively employed in the MOCVD of a GaN film. In addition, the organogallium compound of the present invention may be advantageously used in preparing a GaN film having an improved quality which is suitable for a wide range of semiconductor devices such as blue electroluminescent diodes and blue laser materials.

Claims

1. An organogallium compound of formula(I):



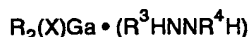
wherein, R^1 and R^2 are each independently C_{1-5} alkyl; and R^3 and R^4 are each independently hydrogen or C_{1-5} alkyl.

2. The compound of claim 1, wherein R^1 and R^2 are the same.

3. The compound of claim 2, which is selected from the group consisting of azidodimethylgallium • hydrazine, azidodimethylgallium • methylhydrazine, azidodimethylgallium • t-butylhydrazine, azidodiethylgallium • hydrazine, azidodiethylgallium • methylhydrazine and azidodiethylgallium • t-butylhydrazine.

4. A process for preparing the compound recited in claim 2, comprising the steps of:

- (a) reacting a compound of formula(II) and a compound of formula(III) to give a compound of formula(IV), and
(b) reacting the compound of formula(IV) and sodium azide:



wherein, X is halogen; R^3 and R^4 are the same as defined in claim 1; and R is C_{1-5} alkyl.

5. The process of claim 4, wherein step (a) is conducted in an organic solvent selected from the group consisting of tetrahydrofuran, acetonitrile, diethylether, toluene and a mixture thereof, at a temperature ranging from -70 to 10°C.
6. The process of claim 4, wherein step (b) is conducted in an organic solvent selected from the group consisting of tetrahydrofuran, acetonitrile, diethylether, toluene and a mixture thereof, at a temperature ranging from 70 to 100 °C.
7. A process for depositing a GaN film on a substrate which comprises bringing the vapor of the compound of claim 1 into contact with a substrate heated to a temperature ranging from 400 to 800°C.
8. The process of claim 7, wherein the compound is vaporized at a temperature ranging from 40 to 100°C.
9. The process of claim 7, wherein the substrate is a single crystal of silicon.

Patentansprüche

1. Eine organische Galliumverbindung der Formel (1):



wobei R¹ und R² jeweils unabhängig C₁₋₅ Alkyl und R³ und R⁴ jeweils unabhängig Wasserstoff oder C₁₋₅ Alkyl sind.

2. Verbindung nach Anspruch 1, bei der R¹ und R² die gleichen sind

5 3. Verbindung nach Anspruch 2, die aus der Gruppe ausgewählt ist, die aus Azidodimethylgallium-Hydrazin, Azidodimethylgallium-Methylhydrazin, Azidodimethylgallium-t-Butyl-hydrazin, Azidodiethylgallium-Hydrazin, Azidodiethylgallium-Methylhydrazin und Azidodiethylgallium-t-Butylhydrazin besteht.

10 4. Verfahren zur Herstellung der in Anspruch 2 wiedergegebenen Verbindung, das die Schritte umfaßt von:

(a) Umsetzen einer Verbindung der Formel (II) und einer Verbindung der Formel (III), um eine Verbindung der Formel (IV) zu ergeben und

15 (b) Umsetzen der Verbindung der Formel (IV) und Natriumazid:



25 wobei X Halogen ist, R³ und R⁴ die gleichen sind, wie in Anspruch 1 definiert und R C₁₋₅ Alkyl ist.

5. Verfahren nach Anspruch 4, bei dem der Schritt (a) in einem organischen Lösungsmittel durchgeführt wird, das aus der Gruppe ausgewählt ist, die aus Tetrahydrofuran, Acetonitril, Diethyläther, Toluol und einer Mischung dieser besteht, bei einer Temperatur im Bereich von -70 bis 10°C.

30 6. Verfahren nach Anspruch 4, bei dem der Schritt (b) in einem organischen Lösungsmittel durchgeführt wird, das aus der Gruppe ausgewählt ist, die aus Tetrahydrofuran, Acetonitril, Diethyläther, Toluol und eine Mischung dieser besteht, bei einer Temperatur im Bereich von -70 bis 100°C.

35 7. Verfahren zum Ablagern eines GaN-Films auf einem Substrat, welches das Bringen des Dampfes der Verbindung von Anspruch 1 in Kontakt mit einem Substrat umfaßt, das auf eine Temperatur im Bereich von 400-800°C erwärmt ist.

40 8. Verfahren nach Anspruch 7, bei dem die Verbindung bei einer Temperatur im Bereich von 40-100°C verdampft wird.

9. Verfahren nach Anspruch 7, bei dem das Substrat ein Einkristall aus Silizium ist.

Revendications

45 1. Composé organogallium de formule (I):



50 dans laquelle R¹ et R² sont chacun indépendamment un groupe alkyle en C₁-C₅; et R³ et R⁴ sont chacun indépendamment un hydrogène ou un groupe alkyle en C₁-C₅.

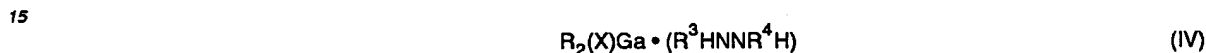
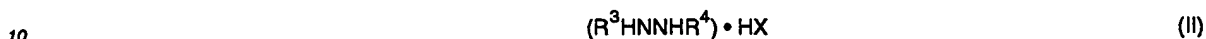
55 2. Composé selon la revendication 1, dans lequel R¹ et R² sont identiques.

3. Composé selon la revendication 2, qui est choisi dans le groupe constitué des composés azidodiméthylgallium-hydrazine, azidodiméthylgallium-méthylhydrazine, azidodiméthylgallium-t-butylhydrazine, azidodiéthylgallium-

hydrazine, azidodiéthylgallium - méthylhydrazine et d'azidodiéthylgallium - t-butylhydrazine.

4. Procédé de préparation du composé selon la revendication 2, comprenant les étapes de :

- 5 (a) mettre à réagir un composé de formule (II) et un composé de formule (III) pour obtenir un composé de formule (IV), et
(b) mettre à réagir le composé de formule (IV) et l'azoture de sodium :



20 dans laquelle X est un halogène; R^3 et R^4 sont tels que définis en revendication 1 ; et R est un groupe alkyle en C_1-C_5 .

5. Procédé selon la revendication 4, dans lequel l'étape (a) est conduite dans un solvant organique choisi dans le groupe constitué du tétrahydrofurane, acétonitrile, diéthyléther, toluène et de leur mélange, à une température variant de -70 à 10°C.
- 25 6. Procédé selon la revendication 4, dans lequel l'étape (b) est conduite dans un solvant organique choisi dans le groupe constitué du tétrahydrofurane, acétonitrile, diéthyléther, toluène et de leur mélange, à une température variant de 70 à 100°C.
- 30 7. Procédé de dépôt d'un film de GaN sur un substrat qui comprend la mise en contact de la vapeur du composé selon la revendication 1 avec un substrat chauffé à une température variant de 400 à 800°C.
8. Procédé selon la revendication 7, dans lequel le composé est vaporisé à une température variant de 40 à 100°C.
- 35 9. Procédé selon la revendication 7, dans lequel le substrat est un monocristal de silicium.

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FIG. 1

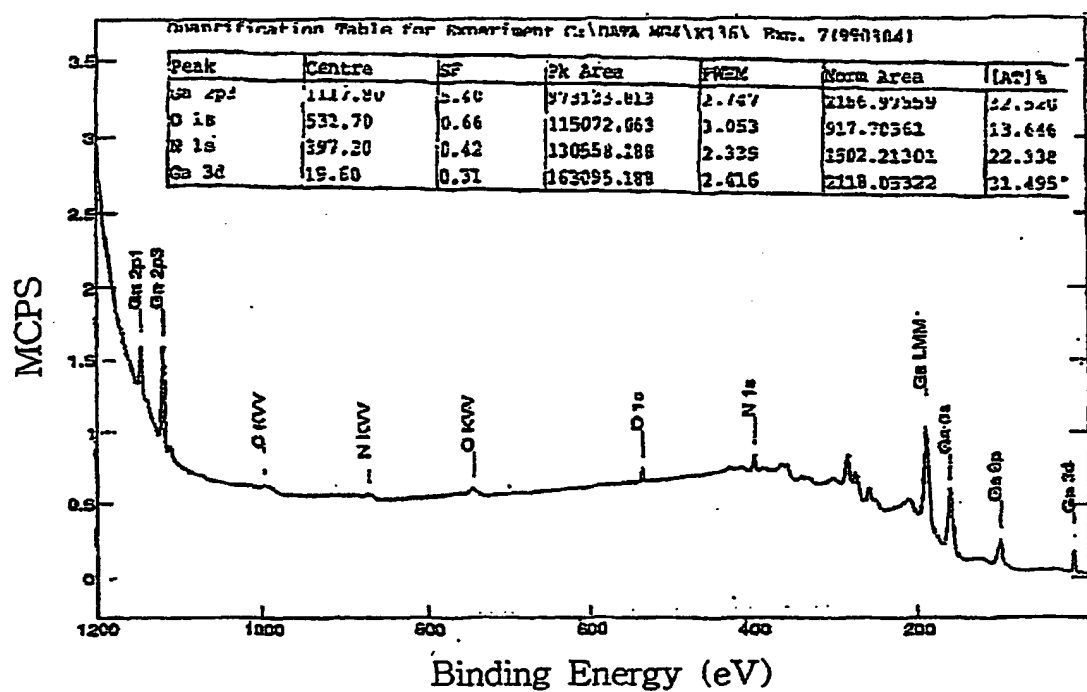


FIG. 2

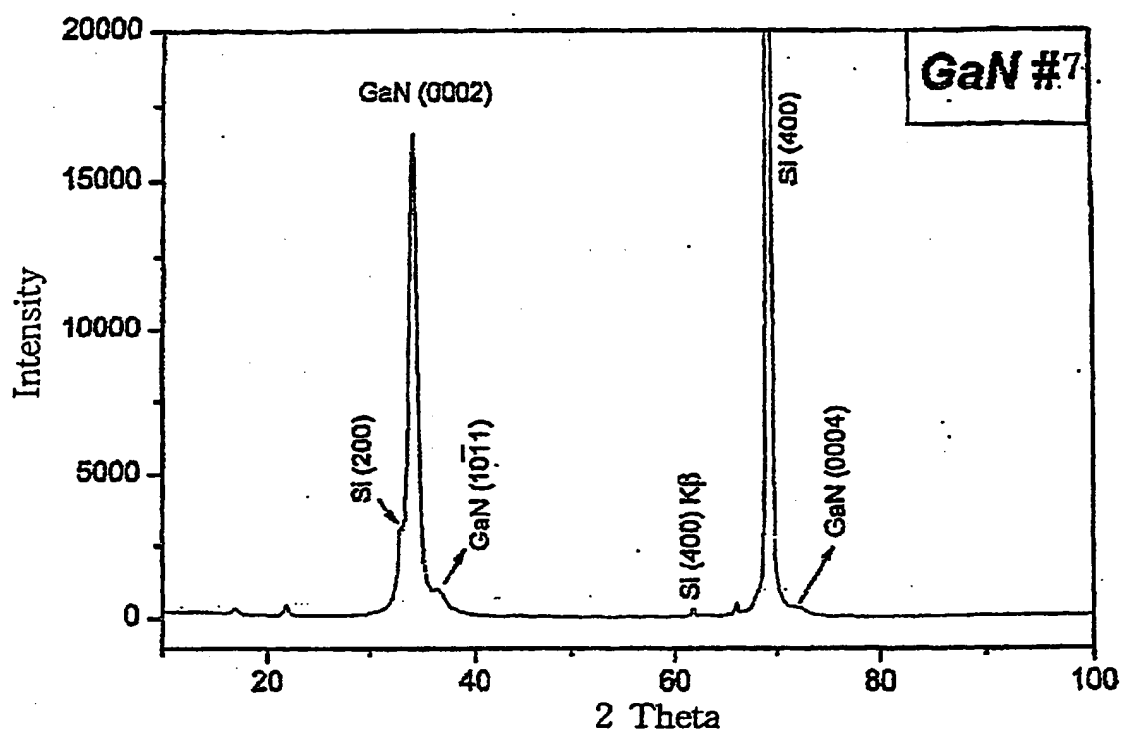


FIG. 3

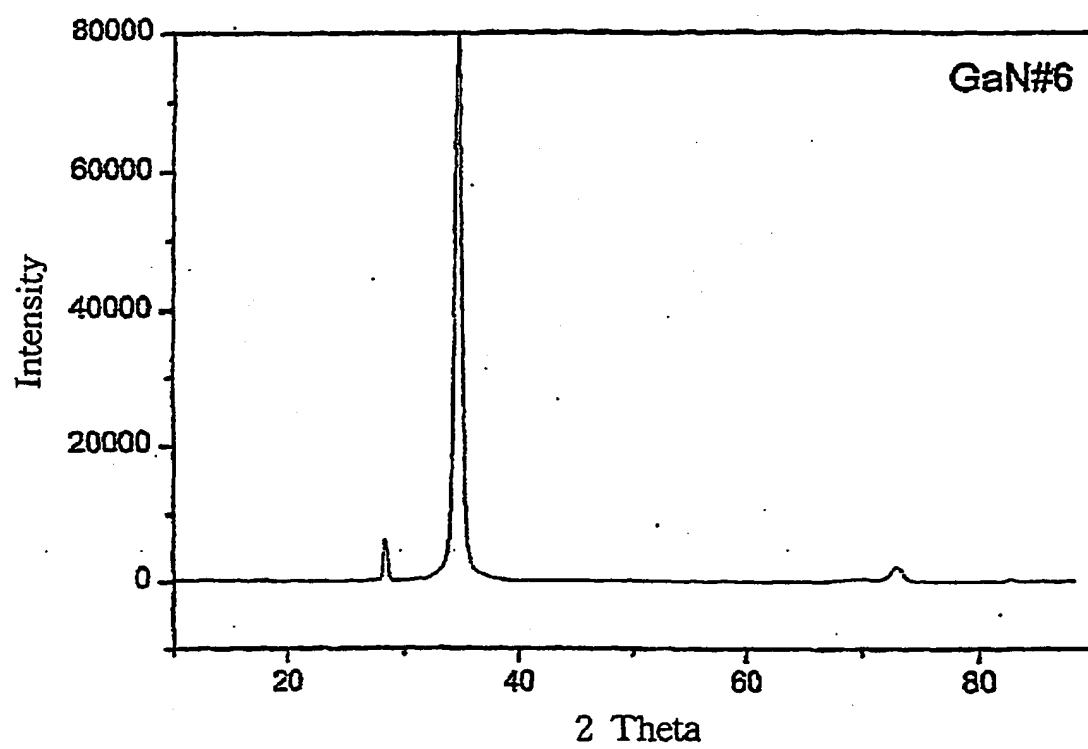


FIG. 4

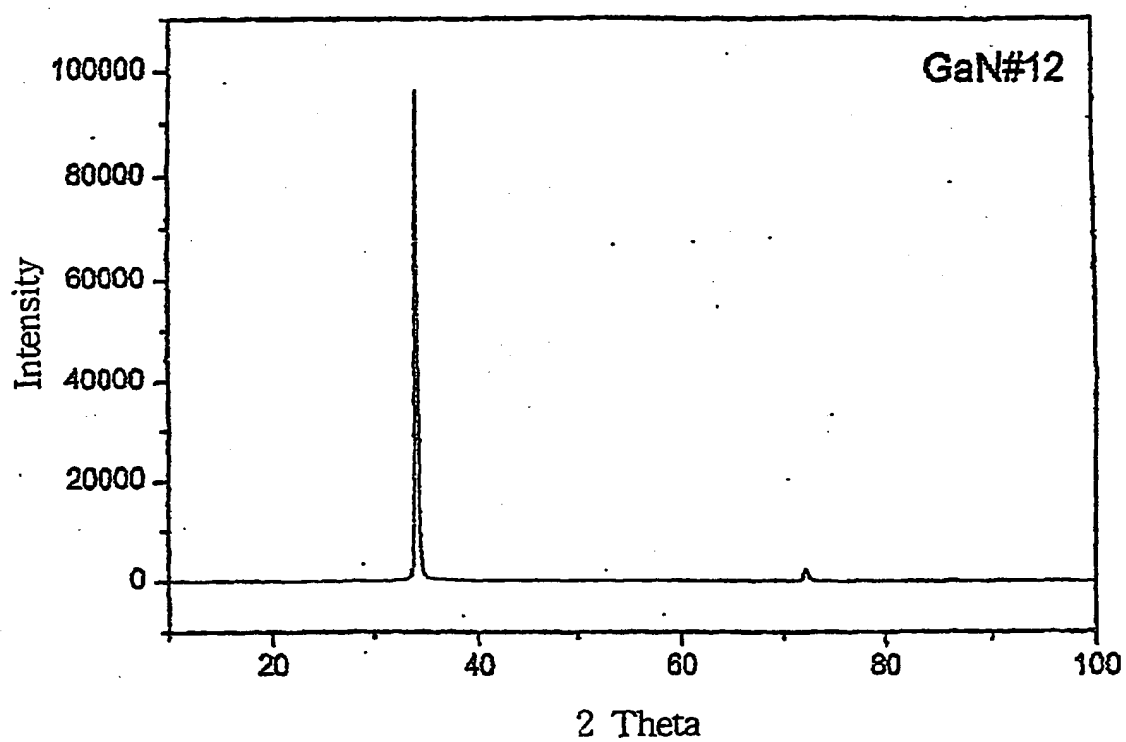


FIG.5

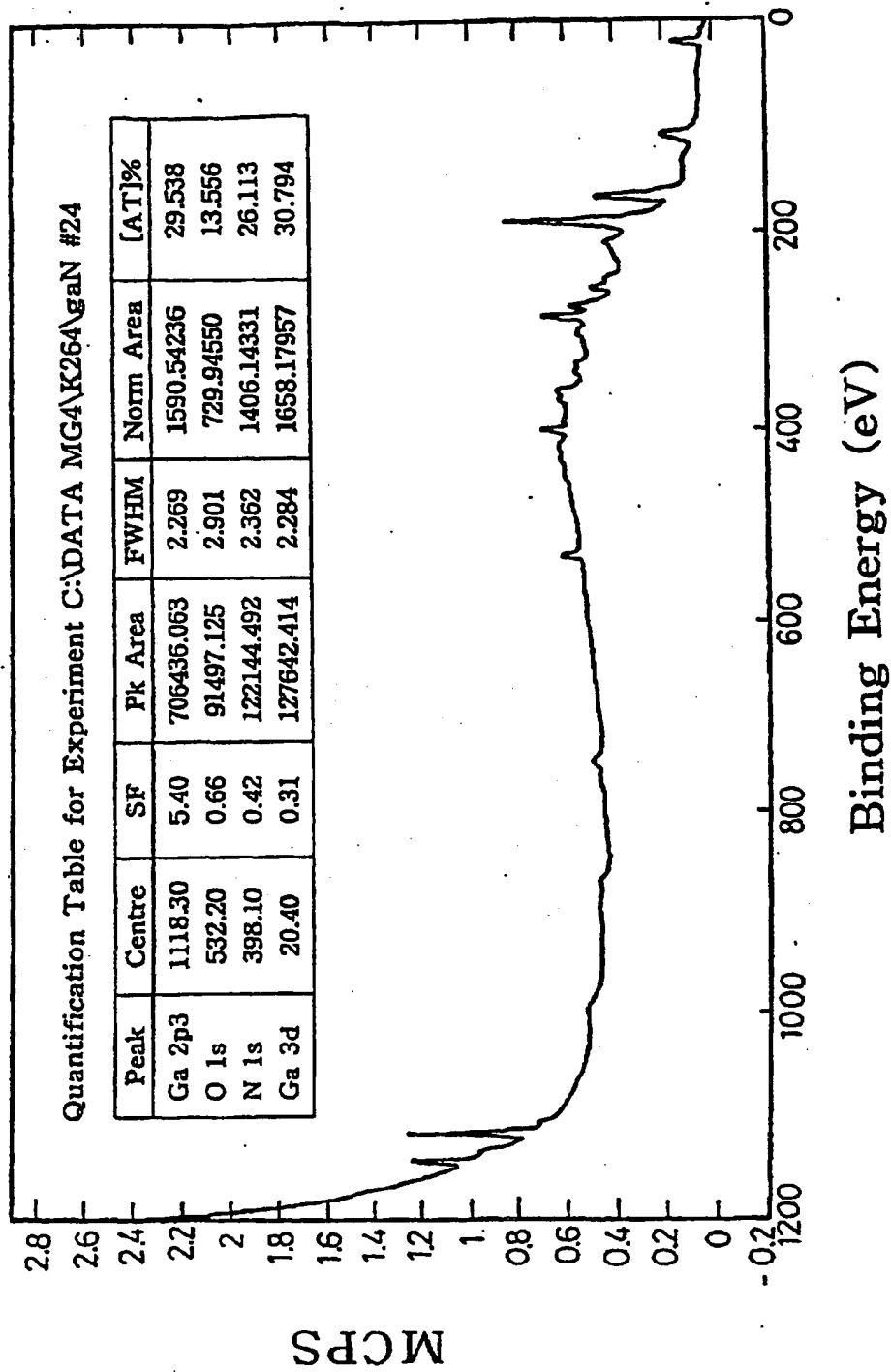


FIG. 6

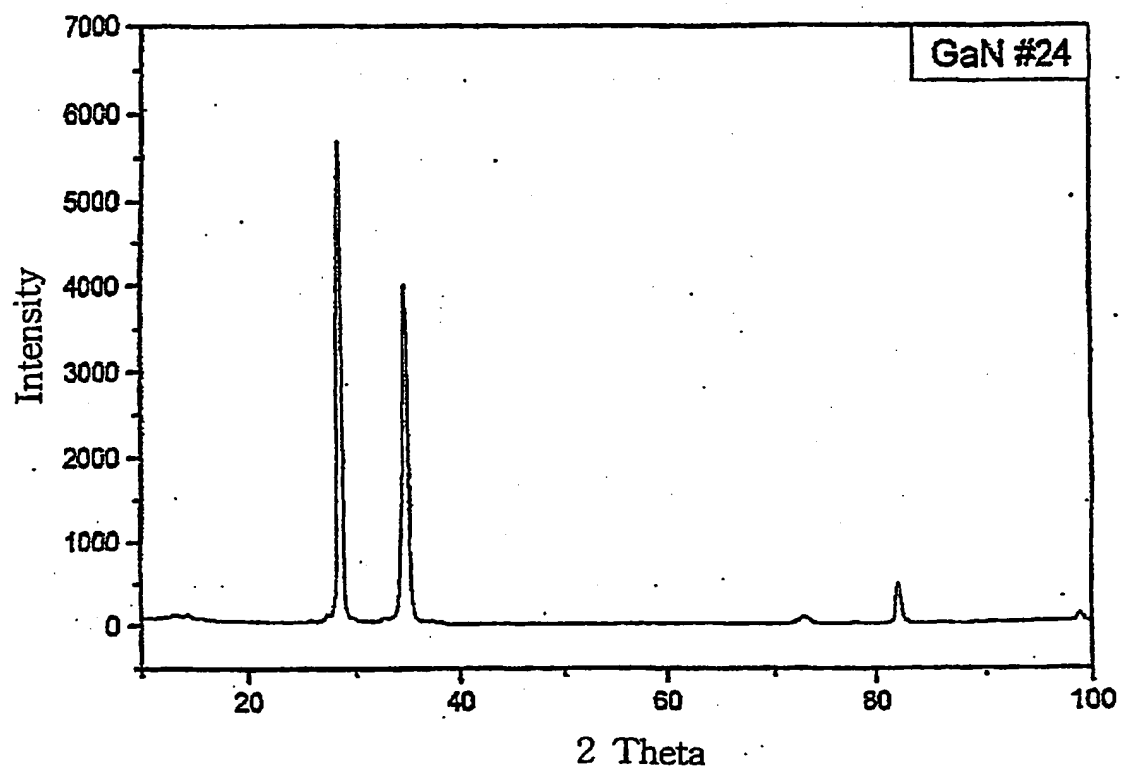


FIG. 7

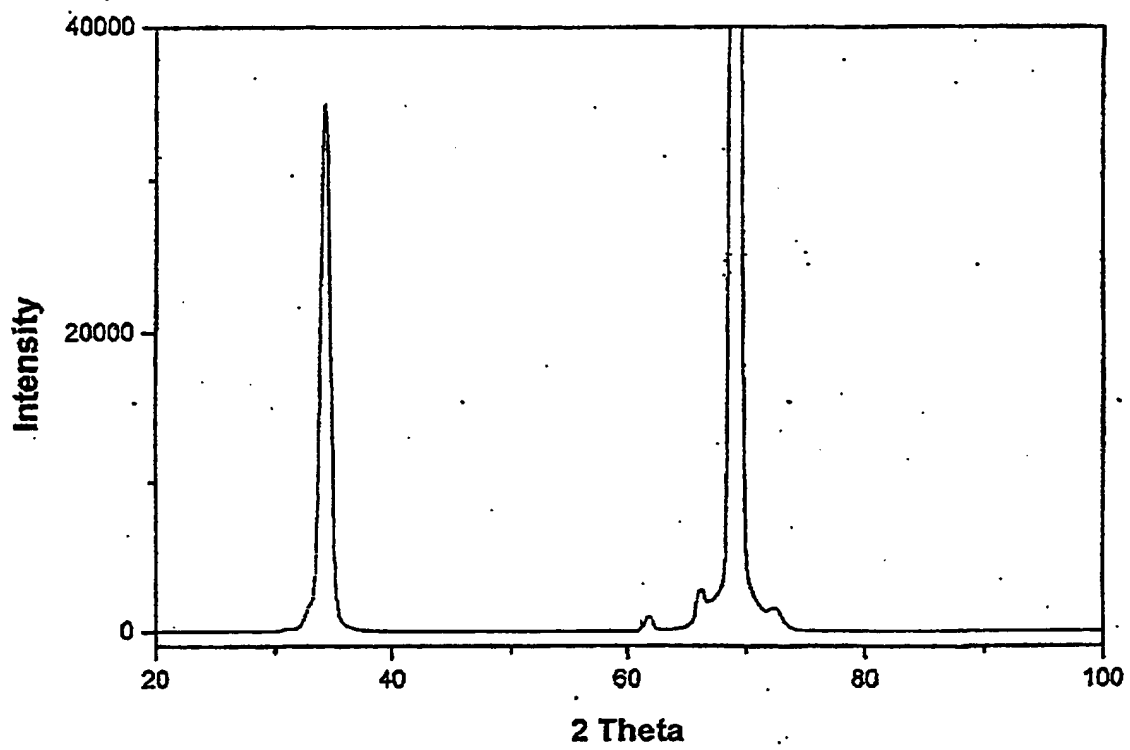
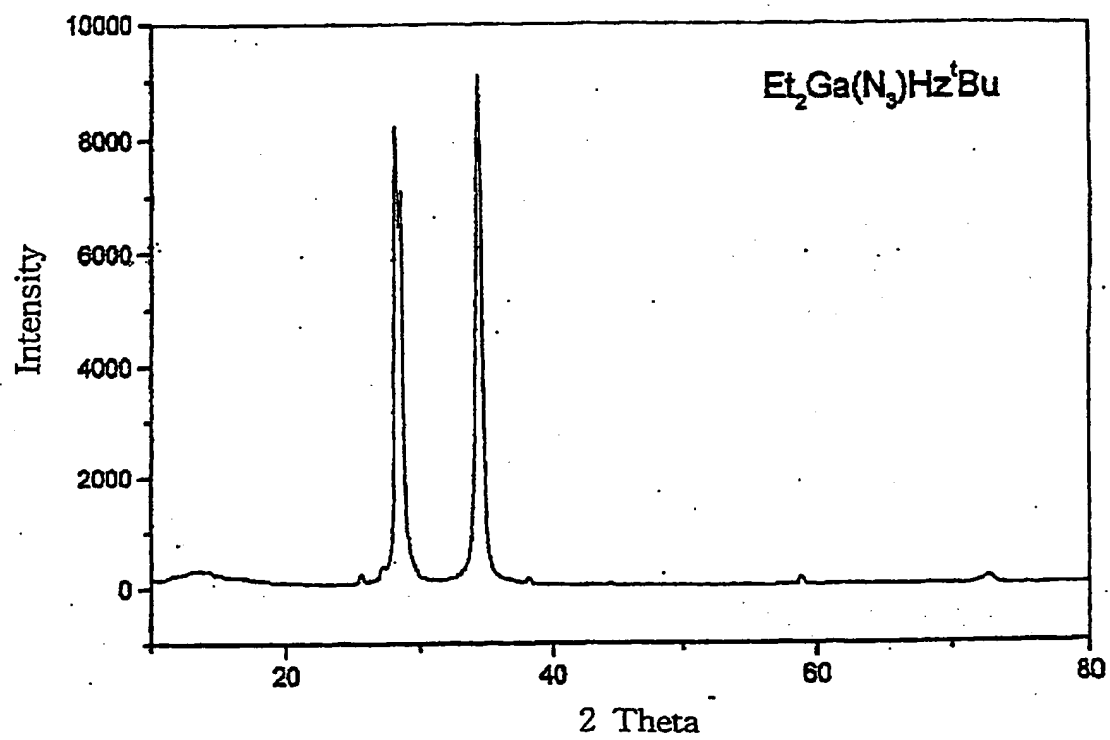


FIG. 8



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